

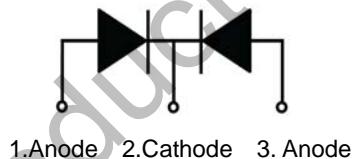
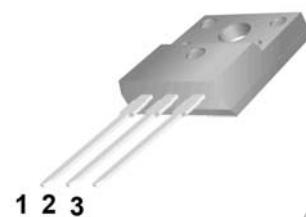


MBRF10100VCT

Features:

- Low power loss
- Low forward voltage .
- High surge capacity
- High efficiency
- Metal silicon junction

TO-220F



Absolute Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	V
Maximum RMS Voltage	V_{RMS}	70	V
Maximum DC Blocking Voltage	$V_{R(DC)}$	100	V
Maximum Average Forward Current (per device)	$I_{F(AV)}$	10	A
Peak Forward Surge Current: 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	120	A
Maximum Forward Voltage @ $IF=5A_{pk}$, $T_j=125^\circ\text{C}$	V_F	0.65	V
Maximum DC Reverse Current T _j =25°C	I_R	0.1	mA
		20	mA
Maximum Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65~+150	°C

Typical Characteristics

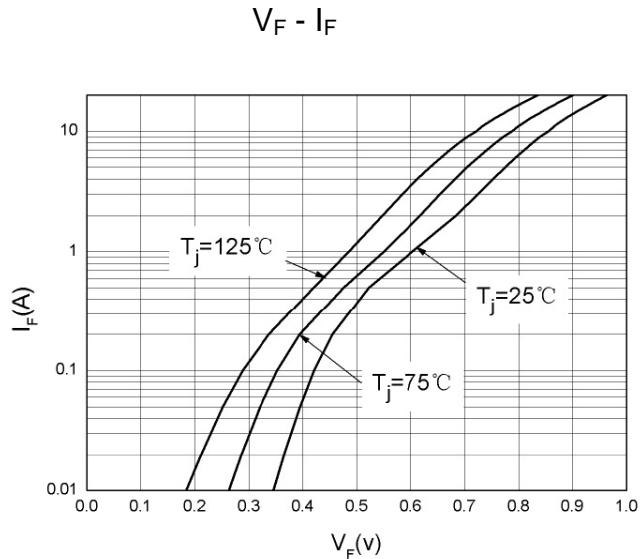


Fig 1. TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC

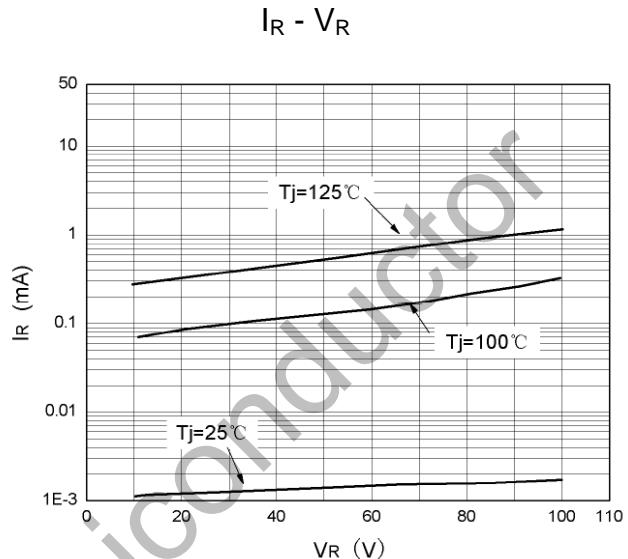


Fig 2. TYPICAL REVERSE CHARACTERISTIC

Package Dimension

TO-220F

Unit: mm

